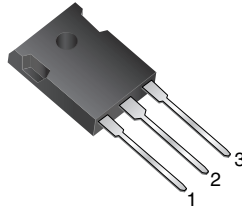
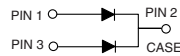


Dual Common Cathode Ultrafast Rectifier



TO-247AD (TO-3P)



FEATURES

- Glass passivated chip junction
- Ultrafast recovery time
- Low switching losses, high efficiency
- Low thermal resistance
- High forward surge capability
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, inverters, freewheeling diodes, dc-to-dc converters, and other power switching application.

MECHANICAL DATA

Case: TO-247AD (TO-3P)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	30 A
V_{RRM}	50 V to 600 V
I_{FSM}	300 A
t_{rr}	35 ns, 50 ns
V_F	0.95 V, 1.3 V, 1.5 V
$T_J \text{ max.}$	150 °C

MAXIMUM RATINGS ($T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	FEP 30AP	FEP 30BP	FEP 30CP	FEP 30DP	FEP 30FP	FEP 30GP	FEP 30HP	FEP 30JP	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	300	400	500	600	V
Maximum average forward rectified current at $T_C = 100\text{ °C}$	$I_{F(AV)}$	30								A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	300								A
Operating storage and temperature range	T_J, T_{STG}	- 55 to + 150								°C/W

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)											
PARAMETER	TEST CONDITIONS	SYMBOL	FEP 30AP	FEP 30BP	FEP 30CP	FEP 30DP	FEP 30FP	FEP 30GP	FEP 30HP	FEP 30JP	UNIT
Maximum instantaneous forward voltage per diode	15.0 A	V _F	0.95			1.3		1.5			V
Maximum DC reverse current at rated DC blocking voltage per diode	T _C = 25 °C T _C = 100 °C	I _R	10			500					μA
Maximum reverse recovery time per diode	I _F = 0.5 A, I _R = 1.0 A, I _{rr} = 0.25 A	t _{rr}	35			50					ns
Typical junction capacitance per diode	4.0 V, 1 MHz	C _J	175					145			pF

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)										
PARAMETER	SYMBOL	FEP 30AP	FEP 30BP	FEP 30CP	FEP 30DP	FEP 30FP	FEP 30GP	FEP 30HP	FEP 30JP	UNIT
Typical thermal resistance per diode ⁽¹⁾	R _{θJC}	1.0								°C/W

Note:

(1) Thermal resistance from junction to case per diode mounted on heatsink

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-247AD	FEP30JP-E3/45	6.15	30	30/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

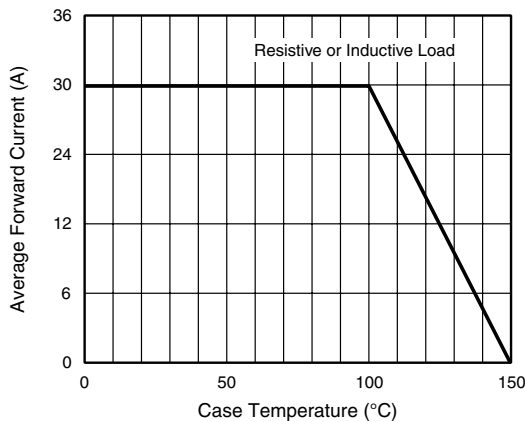


Figure 1. Forward Current Derating Curve

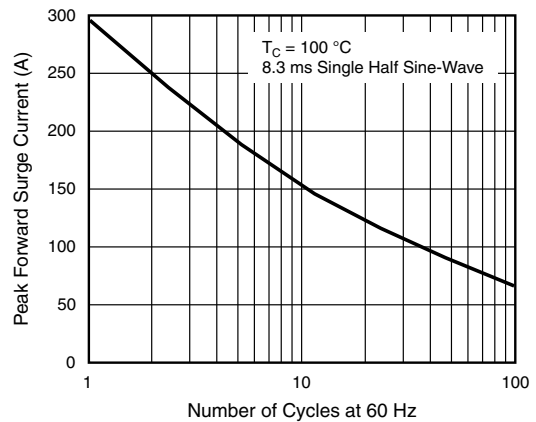


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

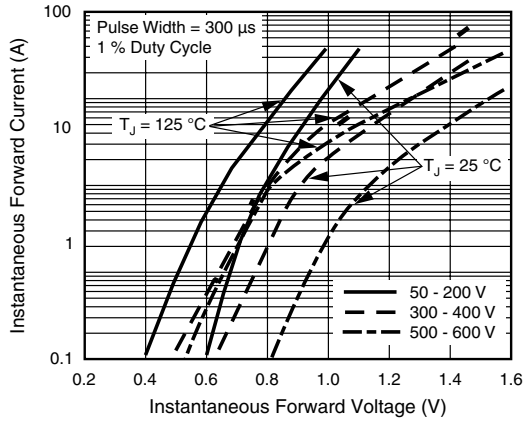


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

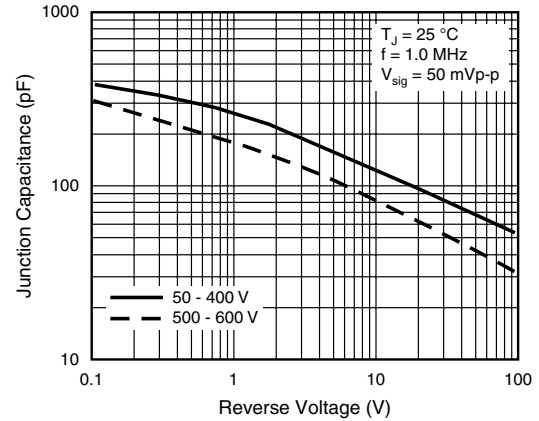


Figure 5. Typical Junction Capacitance Per Diode

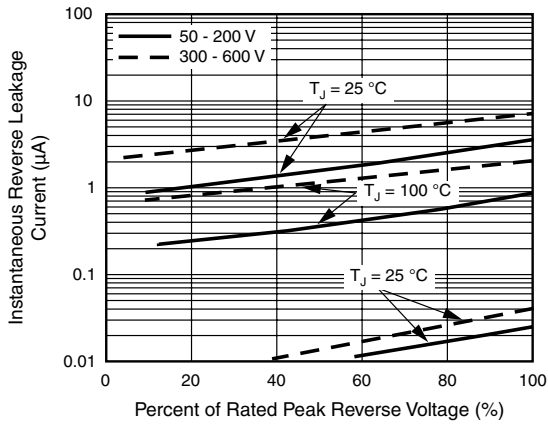


Figure 4. Typical Reverse Characteristics Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

TO-247AD (TO-3P)

